IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Masayuki HATA, et al.

Serial No.:

Group Art Unit:

Filed: February 25, 2002

Examiner:

For:

NITRIDE-BASED SEMICONDUCTOR ELEMENT AND METHOD OF FORMING

NITRIDE-BASED SEMICONDUCTOR

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents Washington, DC 20231

Dear Sir:

In accordance with the provisions of 37 C.F.R. 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the documents listed on the attached form PTO-1449. It is respectfully requested that the documents be expressly considered during the prosecution of this application, and that the documents be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This Information Disclosure Statement is being filed within three months of the U.S. filing date OR before the mailing date of a first Office Action on the merits. No certification or fee is required.

Respectfully submitted,

MCDERMOTT, WILL & EMERY

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SHEET <u>1</u> OF <u>1</u>

INFORMATION DISCLOSURE CITATION IN AN APPLICATION				ATTY. DOCKET NO. 57810-032		serial no. ota ota ota al.		
				APPLICANT Masayuki HATA, et al.				
(PTO-1449)				FILING DATE February 25, 2002		GROUP U		
U.S. PATENT DOCUMENTS								
EXAMINER'S INITIALS	PATENT NO.	DATE		NAME	CLASS	SUBCLASS	FILING DATE	
	6,153,010	11/28/2000	Kiyoku et al.					
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FOREIGN PATENT DOCUMENTS Translation Translation								
EXAMINER'S INITIALS	PATENT NO.	DATE	C	COUNTRY	CLASS	SUBCLASS	Yes No	
							ies	
•	15 Apr - 2.							
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)								
	Robert F. Davis et al., "Pendeo-epitaxial Growth and Characterization of Gallium Nitride and Related Materials", Technical Digest, International Workshop on Nitride Semiconductors, IWN2000, September 24-27, 2000, pp. 79-81.							
	Kazuyuki TADATOMO, "High Output Power InGaN Ultraviolet Light-Emitting Diodes Fabricated on Patterned Substrates Using Metalorganic Vapor Phase Epitaxy", Jpn. J. Appl. Phys., Vol. 40, (2001), pp. L583-L585.							
EXAMINER				DATE CONSIDERED				